Level	#	Requirement Summary	TE101	TE102	TE103	TE201	TE202	TE203	TE204	TE205	TE206	TE301	TE401	TE501	TE502	TE503	TE504	SVAC	Notes
3	5.7	Single layer dead channel < 1%, eff. > 99%																	New TKR test (next rev.)
3	5.8	MIP direction measured to better than 0.2 deg																x	
3	5.10	single / double MIP separation at better than 1 sigma																x	
3	5.11.1	6-layer trigger eff > 90%																	New TKR test (next rev.)
3	5.11.2	6-layer trigger noise < 500 Hz																	New TKR test (next rev.)
3	5.11.3	trigger saturation recovery time < 250μs																	GTFE component test ?
3	5.12	data noise occupancy per trigger < 1e-4											x	x	x				
3	5.13	deadtime < 10% at 10 kHz																	New TKR test (next rev.)
3	5.15	power consumption < 185W	x																
3	5.17	Left-right data readout for X channels per module																	New TKR test (next rev.)
3	5.19	X Temperature sensors working per module		x															
4	6.1	strip trigger occ.< 5e-5 within 0.5 ms @ 99% MIP eff											x	x	x				
4	6.2	strip data occ. < 1e-4 per trigger @ 99% MIP eff.											x	x	x				
4	6.3	RMS of thresholds for single GTFE < 10%									x								
4	7.2	Shaping amp. Peaking time 2.0+/-0.5 μs																	GTFE component test
4	7.5	threshold range 0-700mV w/ res. <6mV @ 150mV							x										
4	7.7	TOT per layer measured >40μs w/ res. <0.25μs								x					x				
4	8.1	Register configuration control working			x	x													
4	8.2	Register configuration readback working			x	x													
4	8.5	Hard reset line working						x											
4	8.8	Single layer trigger timing jitter < 250ns for >2.6fC										x							
4	8.10	Single GTRC and GTFE commanding working																	GTRC component test
4	8.11	Broadcast command to all GTRC or GTFE working					x												
4	9.2	Charge injection working																	GTFE component test
4	9.3	Internal calibration range from 0-40fC w/ res <0.25fC																	GTFE component test
4	10.1	At least 8 temperature sensors working, all 4 sides		x															
4	11.2	Switch of bias voltage to individual sides working			x														
4	12	power consumption < 185W	x																
4	13.3	Digital readout does not cause signals in amplifiers												x					
4	14.5	Redundant power circuit to each layer working																	TMCM component test
4	15.1	No loss of functionality for 10kRad of ionizing rad.																	GTFE component test
4	15.2	No single event latchup at 20MeV-cm^2/mg LET																	GTFE component test
4	15.3	No single event configuration upset during a run																	GTFE component test
		LPT																	
		Duration																	